BAT54ATB DIODE

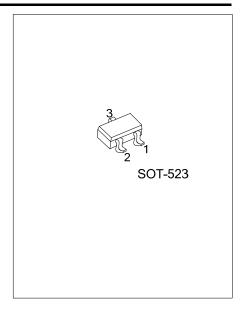
SCHOTTKY BARRIER (DUAL) DIODES

■ DESCRIPTION

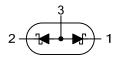
Planar Schottky barrier diodes are encapsulated in the SOT-523 small plastic SMD package. Single diodes and dual diodes with different pin configuration are available.

■ FEATURES

- * Low forward voltage
- * Guard ring protected
- * Small plastic SMD package



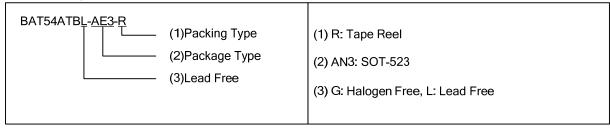
■ SYMBOL



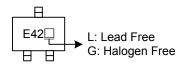
■ ORDERING INFORMATION

| Ordering Number | | Dookogo | Pin Assignment | | | Doolsing | |
|-----------------|-----------------|---------|----------------|----|------|-----------|--|
| Lead Free | Halogen Free | Package | 1 | 2 | 3 | Packing | |
| BAT54ATBL-AN3-R | BAT54ATBG-AN3-R | SOT-523 | K1 | K2 | A2A1 | Tape Reel | |

Note: Pin Assignment: A: Anode K: Cathode



■ MARKING



www.unisonic.com.tw 1 of 3

BAT54ATB DIODE

■ ABSOLUTE MAXIMUM RATINGS

| PARAMETER | SYMBOL | RATINGS | UNIT | | |
|---|------------------|------------|------|--|--|
| PER DIODE | | | | | |
| Continuous Reverse Voltage | V_R | 30 | V | | |
| Continuous Forward Current | I _F | 200 | mA | | |
| Repetitive Peak Forward Current (t _P <1s, δ≤0.5) | I _{FRM} | 300 | mA | | |
| Non-repetitive Peak Forward Current (t _P <10ms) | I _{FSM} | 600 | mA | | |
| Junction Temperature | T_J | +125 | °C | | |
| Storage Temperature | T _{STG} | -60 ~ +150 | °C | | |
| PER DEVICE | | | | | |
| Power Dissipation (T _A ≤25°C) | P_{D} | 230 | mW | | |

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ THERMAL DATA

| PARAMETER | SYMBOL | RATINGS | UNIT |
|---------------------|---------------|---------|------|
| Junction to Ambient | θ_{JA} | 500 | °C/W |

■ **ELECTRICAL CHARACTERISTICS** (T_A = 25°C, unless otherwise specified.)

| PARAMETER | SYMBOL | TEST CONDITIONS | MIN | TYP | MAX | UNIT |
|-----------------------------------|----------------|--|-----|-----|-----|------|
| | V _F | $I_F = 0.1 \text{mA}$ | | | 240 | mV |
| | | I _F = 1mA | | | 320 | mV |
| Forward Voltage (See Fig.1) | | I _F = 10mA | | | 400 | mV |
| | | I _F = 30mA | | | 500 | mV |
| | | I _F = 100mA | | | 800 | mV |
| Reverse Current (See Fig.2) | I_R | V _R = 25V | | | 2 | μΑ |
| Reverse Recovery Time (see Fig.4) | | When switched from I_F =10mA to I_R = 10mA, R_L = 100 Ω measured at I_R = 1mA | | | 5 | ns |
| Diode Capacitance (see Fig.3) | C _D | f = 1 MHz, V _R = 1V; | | | 10 | pF |

BAT54ATB DIODE

■ TYPICAL CHARACTERISTICS

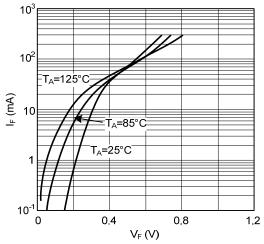


Fig.1 Forward current as a function of forward voltage; typical values.

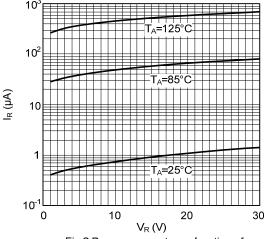


Fig.2 Reverse current as a function of reverse voltage; typical values.

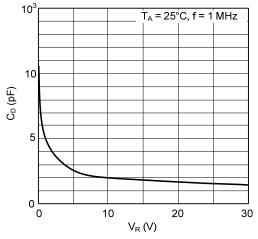


Fig.3 Diode capacitance as a function of reverse voltage; typical values.

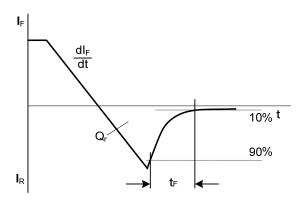


Fig.4 Reverse recovery definitions

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